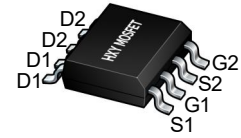




## Description

The DMG4822SSD uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



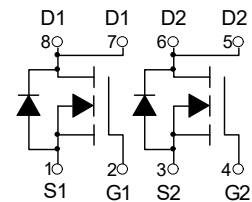
SOP-8

## General Features

$V_{DS} = 30V$   $I_D = 10A$   
 $R_{DS(ON)} < 12m\Omega$  @  $V_{GS}=10V$   
 $R_{DS(ON)} < 18m\Omega$  @  $V_{GS}=4.5V$

## Application

Battery protection  
Load switch  
Uninterruptible power supply



Dual N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMG4822SSD	SOP-8	HXY MOSFET	3000

## Absolute Maximum Ratings@ $T_J=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ C$	Drain Current, $V_{GS}$ @ 4.5V <sup>3</sup>	10	A
$I_D@T_A=70^\circ C$	Drain Current, $V_{GS}$ @ 4.5V <sup>3</sup>	8	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	55	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	62.5	$^\circ C/W$



**Electrical Characteristics Ta = 25 °C**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =250 μ A, V <sub>GS</sub> =0V	30			V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA	
		V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =55 °C			5		
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.5		2.5	V	
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A			12	mΩ	
		V <sub>GS</sub> =10V, I <sub>D</sub> =10A T <sub>J</sub> =125 °C			18		
		V <sub>GS</sub> =4.5 V, I <sub>D</sub> =8A			16.5		
On State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	55			A	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =10A		43		S	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz	610		910	pF	
Output Capacitance	C <sub>oss</sub>		88		160		
Reverse Transfer Capacitance	C <sub>rss</sub>		40		100		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.8		2.4	Ω	
Total Gate Charge (10V)	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =10A	11		17	nC	
Total Gate Charge (4.5V)			5		8		
Gate Source Charge			Q <sub>gs</sub>		2.4		
Gate Drain Charge			Q <sub>gd</sub>		3		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.5Ω, R <sub>GEN</sub> =3Ω		4.4		ns	
Turn-On Rise Time	t <sub>r</sub>			9			
Turn-Off DelayTime	t <sub>d(off)</sub>			17			
Turn-Off Fall Time	t <sub>f</sub>			6			
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10A, di/dt= 500A/us	5.6		8	nC	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		6.4		9.6		
Maximum Body-Diode Continuous Current	I <sub>S</sub>				2.5	A	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V			1	V	

Note.The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.



### Typical Characteristics

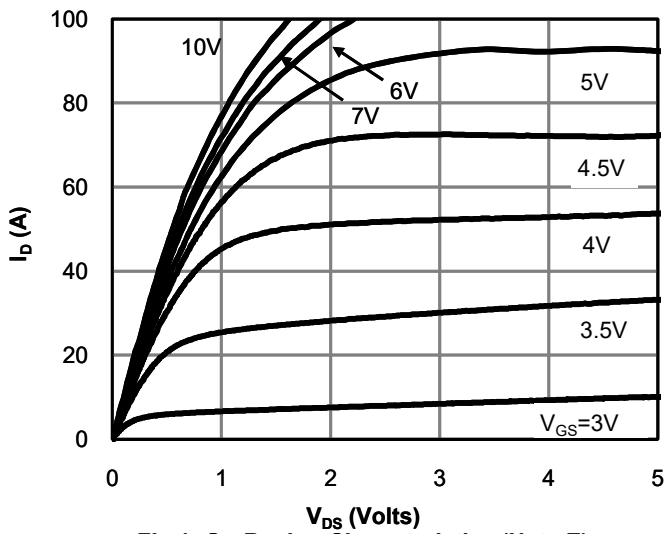


Fig 1: On-Region Characteristics (Note E)

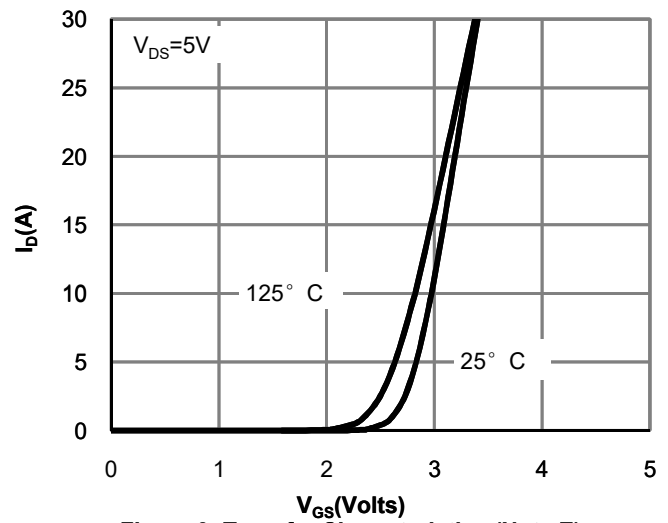


Figure 2: Transfer Characteristics (Note E)

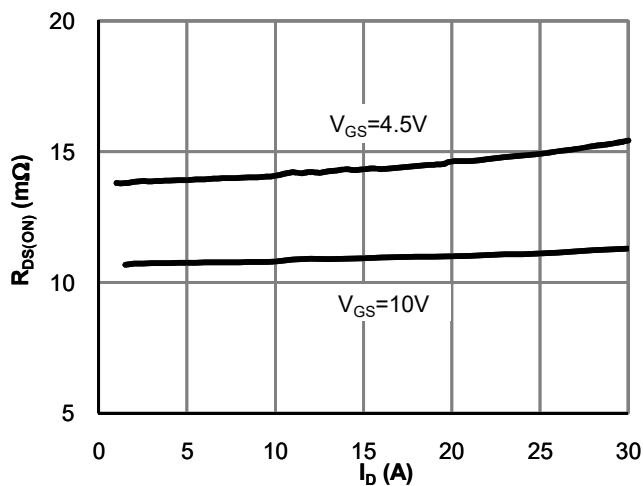


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

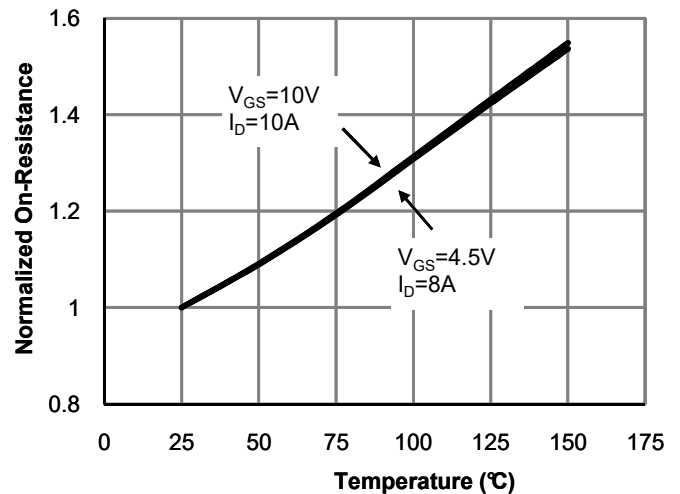


Figure 4: On-Resistance vs. Junction Temperature (Note E)

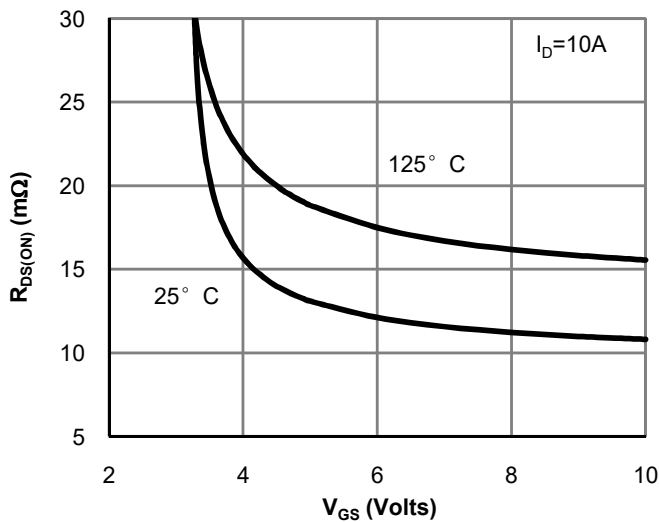


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

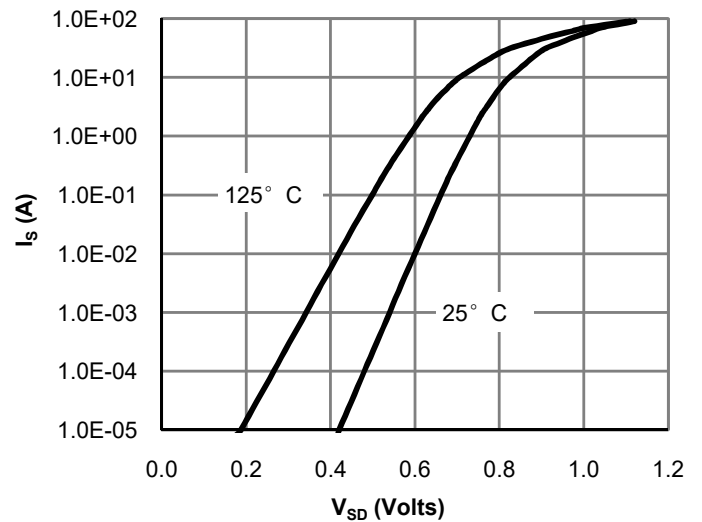


Figure 6: Body-Diode Characteristics (Note E)



Typical Characteristics

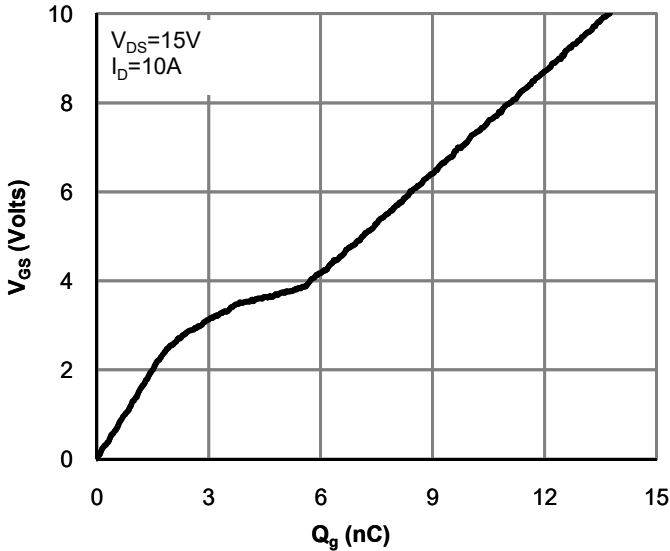


Figure 7: Gate-Charge Characteristics

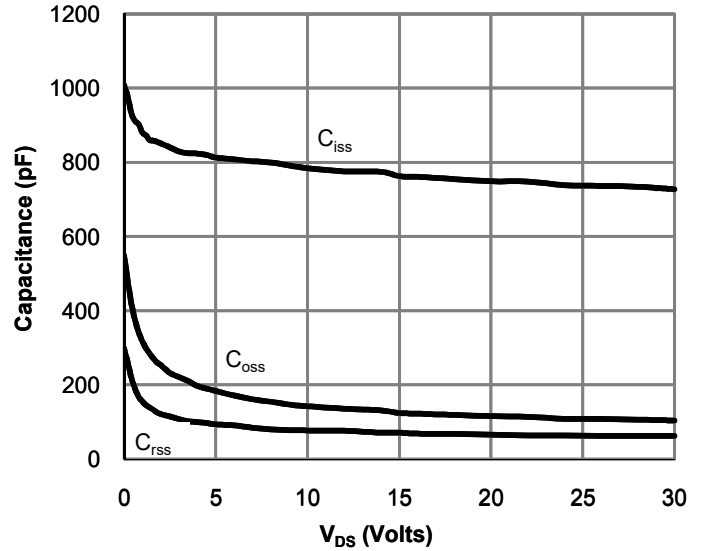


Figure 8: Capacitance Characteristics

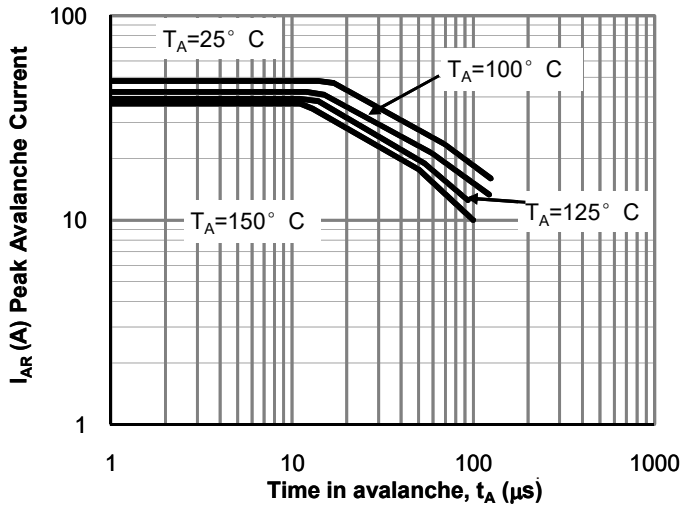


Figure 9: Single Pulse Avalanche capability (Note C)

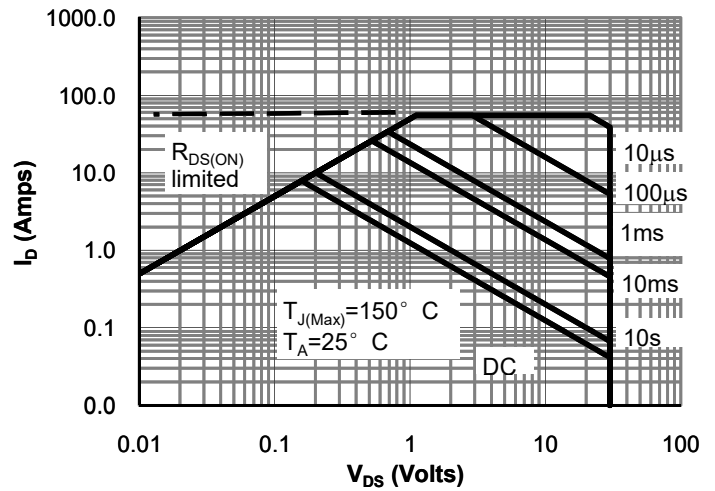


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

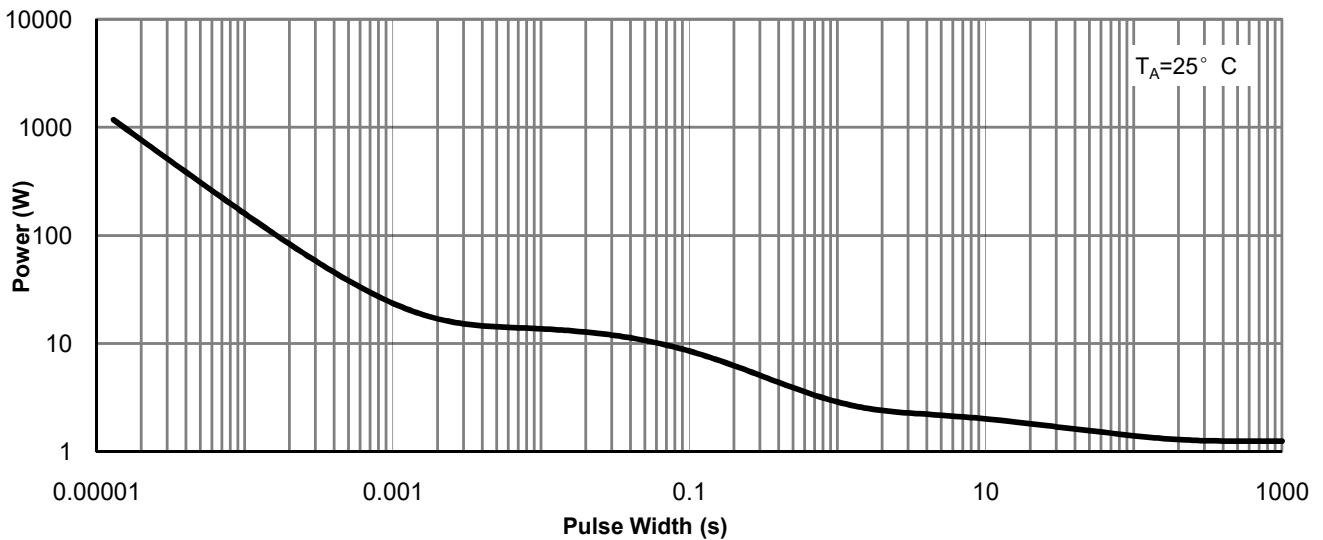


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)



### Typical Characteristics

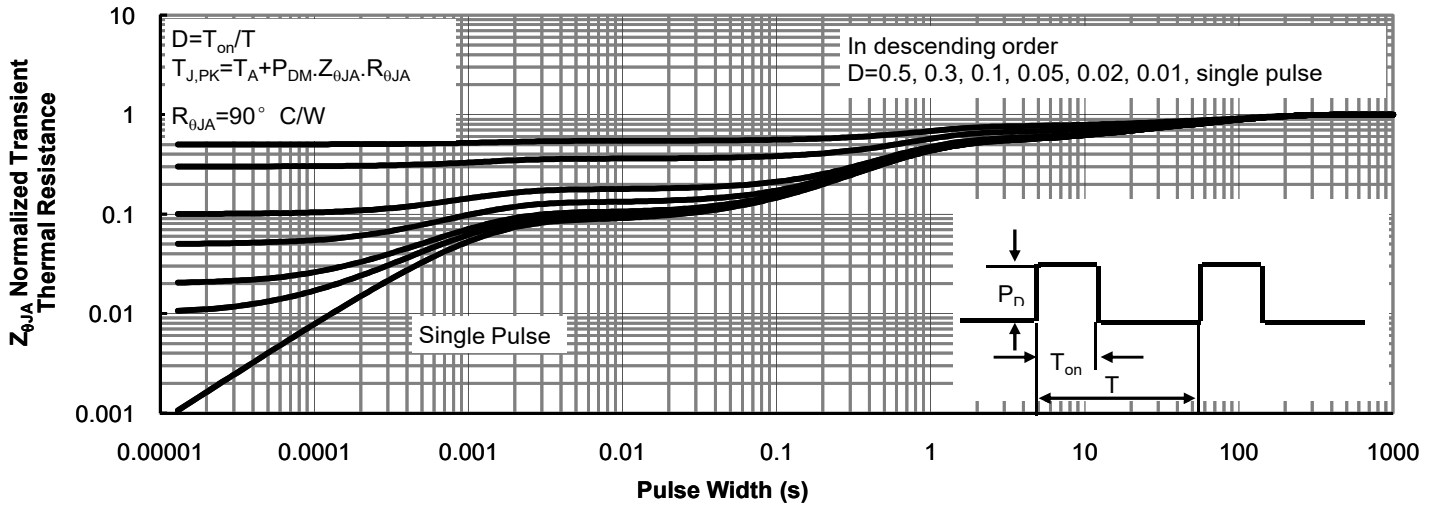
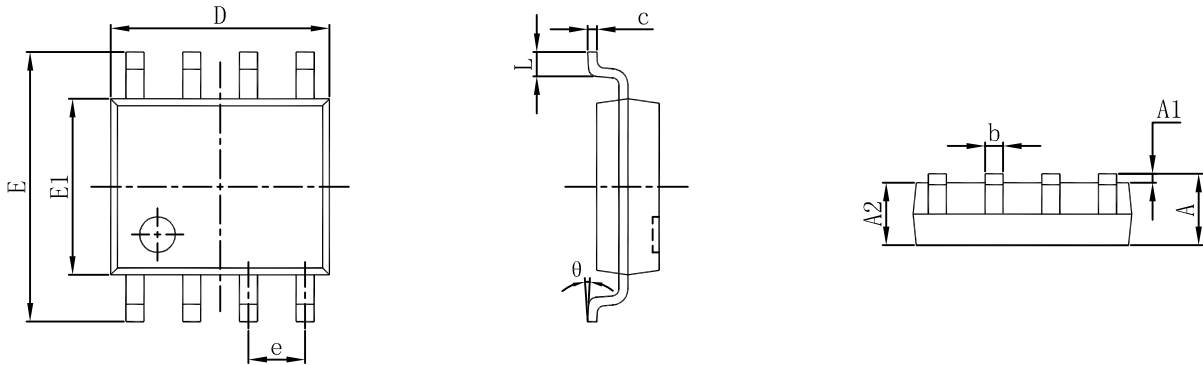


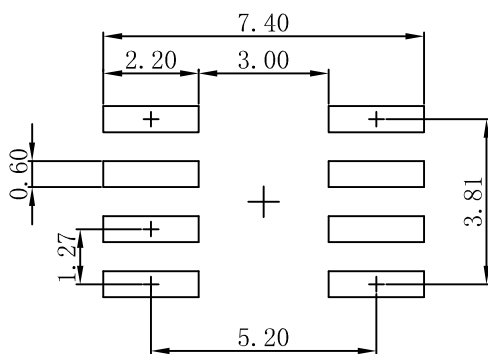
Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)



### SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance:  $\pm 0.05\text{mm}$ .  
 3. The pad layout is for reference purposes only.



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